

Effect of miniaturization on ring-type plasma actuators

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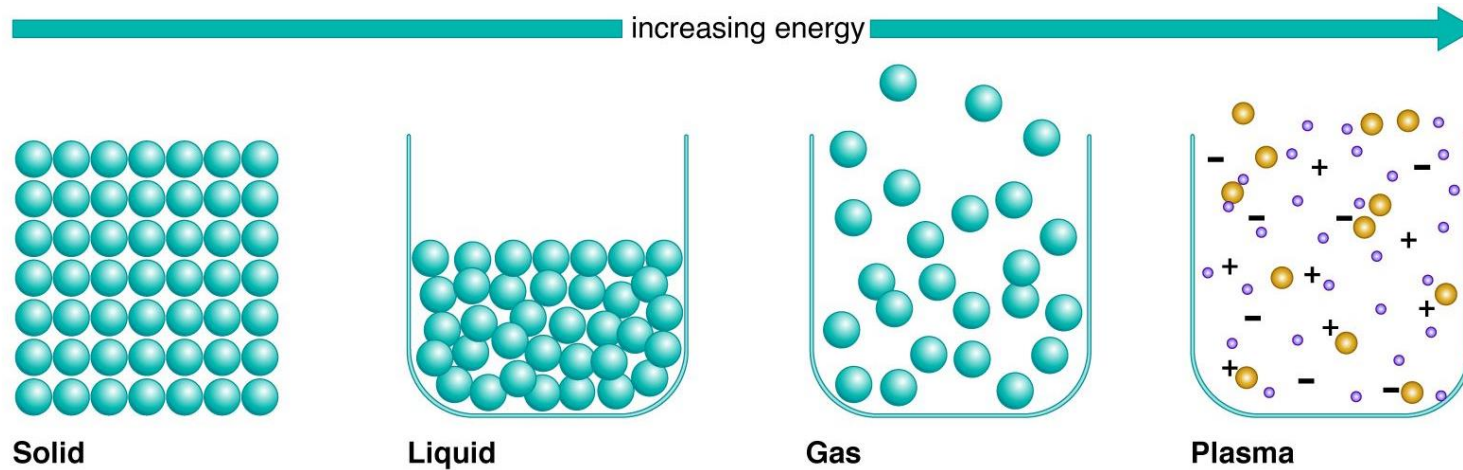
9th ITG International Vacuum Electronics Workshop (IVEW) 2024
August 28 - 30, 2024

Outline

- Introduction
- Motivation
- Experimental setup
- Methodology
- Observation
- Numerical simulations
- Conclusion and outlook

What is plasma?

- Most common medium found in the observable universe
- Widely regarded as the fourth state of matter



Potter, Simeon and Ehlers, Ernest G.. "phase". Encyclopedia Britannica, 29 Mar. 2024

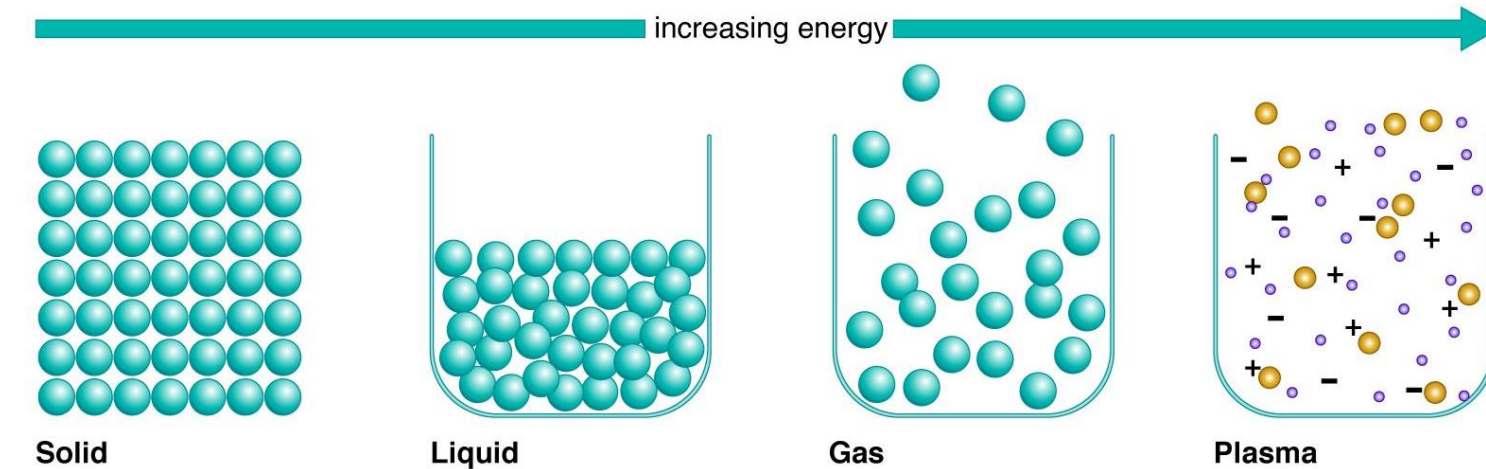
Natural plasmas



www.wikipedia.org

What is plasma?

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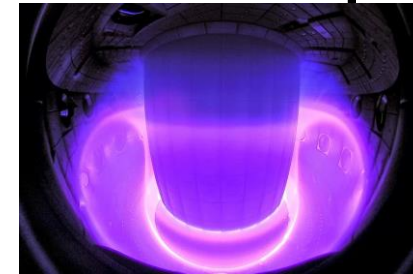


Potter, Simeon and Ehlers, Ernest G.. "phase". Encyclopedia Britannica, 29 Mar. 2024

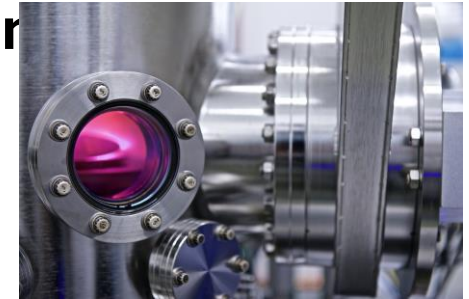
Rigorous definition:

it is a quasineutral gas of charged and neutral particles which exhibits collective behaviour

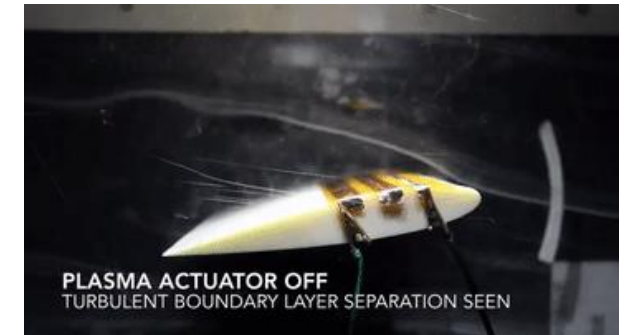
Man-made



www.newscientist.com



<https://www.physik.uni-konstanz.de/>



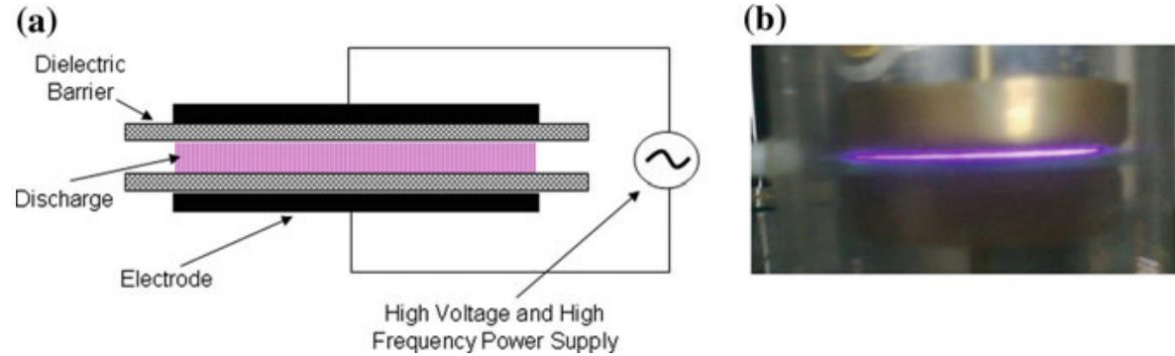
Prince Ghosh (www.youtube.com)



www.uantwerpen.be/en/research-groups/plasmant

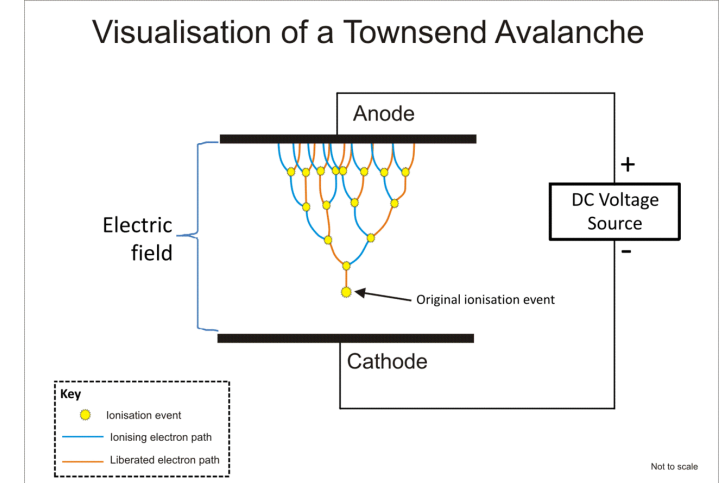
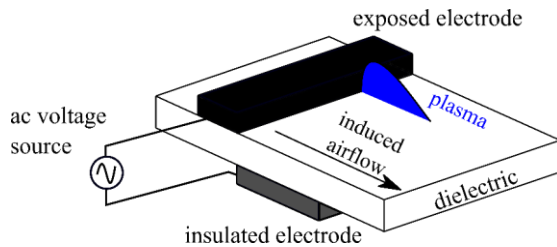
Dielectric Barrier Discharge (DBD)

Volumetric (VDBD)

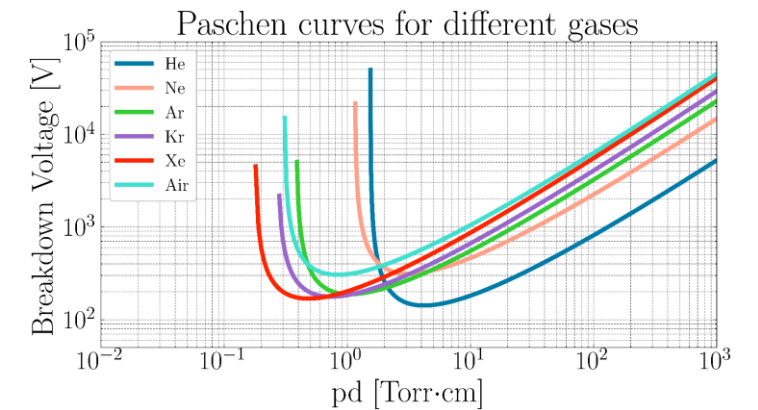


Subedi, D.P., et al., Dielectric Barrier Discharge (DBD) Plasmas and Their Applications. Plasma Science and Technology for Emerging Economies (2017)

Surface (SDBD)



www.wikipedia.org



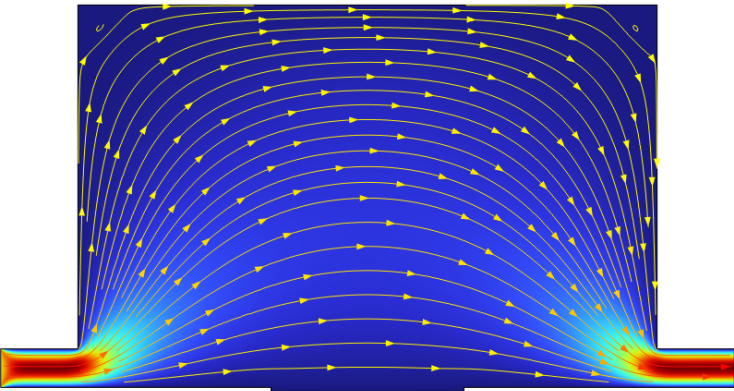
Ionic wind

$$\frac{\partial \rho}{\partial t} + \vec{\nabla} \cdot (\rho \vec{v}) = 0$$

$$\rho \frac{\partial \vec{v}}{\partial t} + \rho (\vec{v} \cdot \vec{\nabla}) \vec{v} = -\vec{\nabla} p + \mu \nabla^2 \vec{v} + \vec{f}_{EHD}$$

↑
 $= e(n_i - n_n - n_e) \vec{E}$

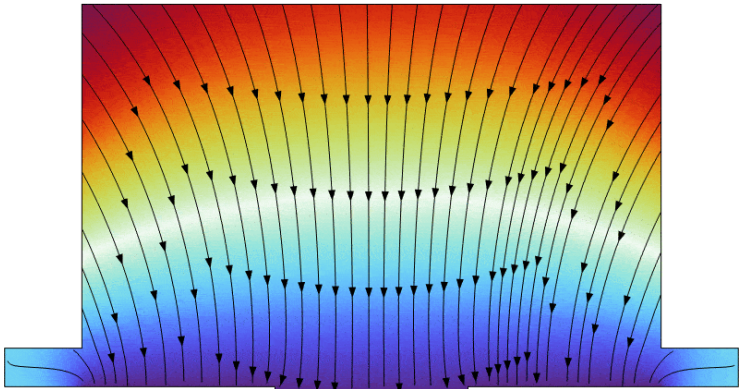
: Surface: Velocity magnitude (m/s) Streamline: Velocity field



Without plasma

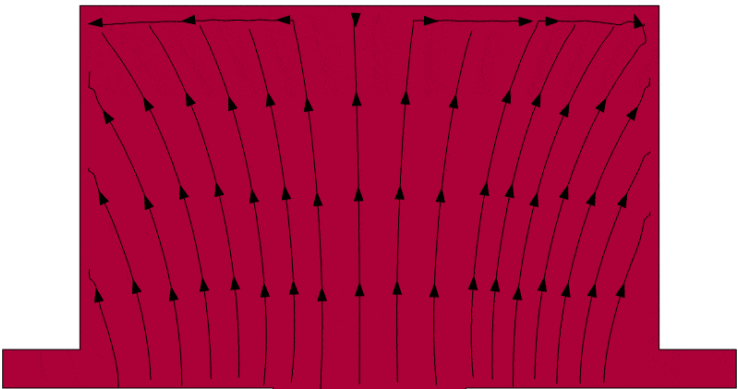
Time=0 s

Surface: Electric potential (V) Streamline: Electric field



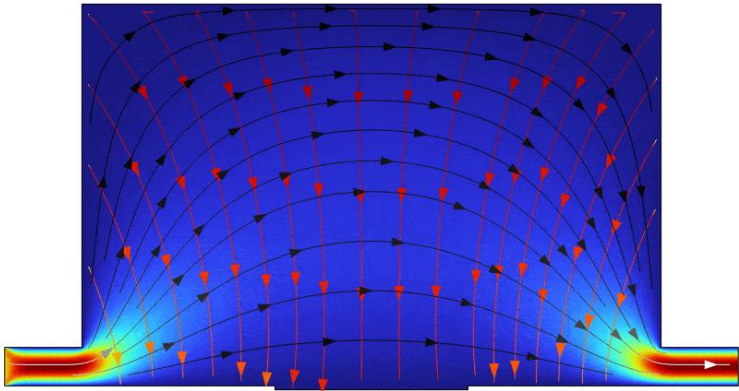
Time=0 s

Surface: Electron density (1/m³) Streamline: Conservative electron flux



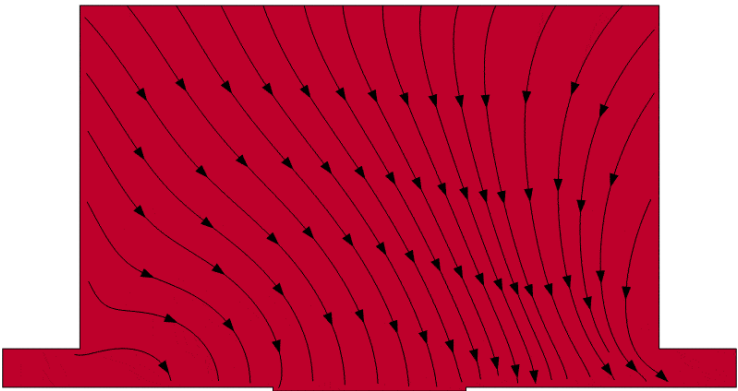
Time=0 s

Surface: Velocity magnitude (m/s) Streamline: Volume force Streamline: Velocity field



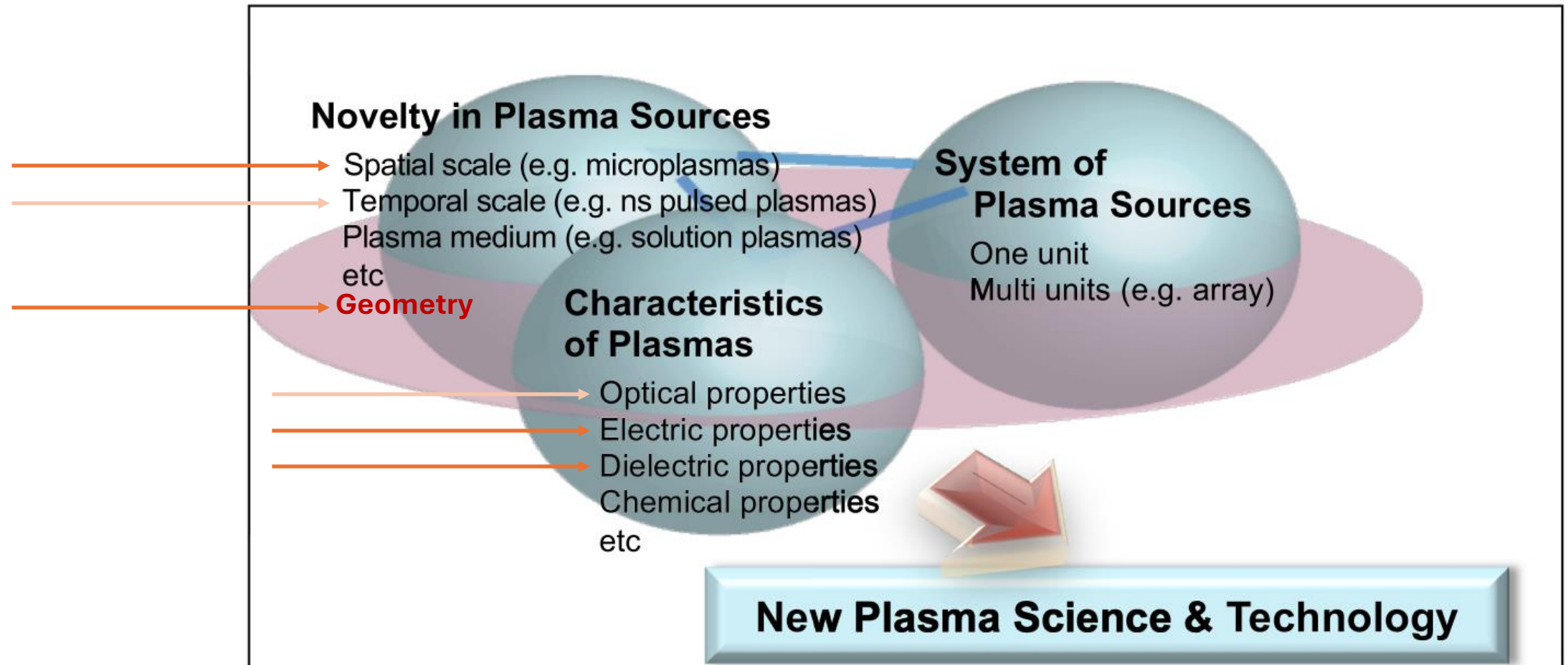
Time=0 s

Surface: Number density (1/m³) Streamline: Total flux



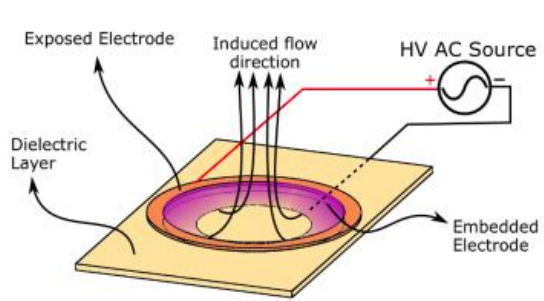
With plasma

Driving force behind new plasma applications and technologies

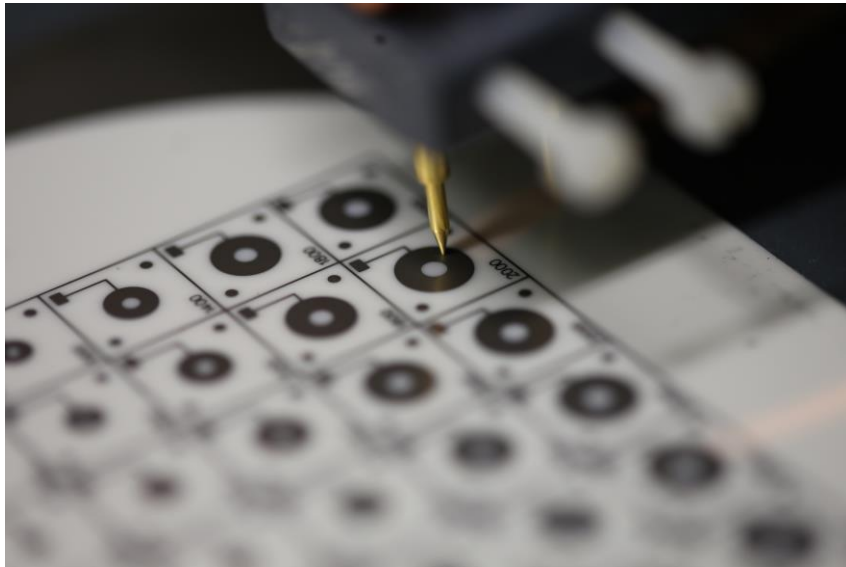
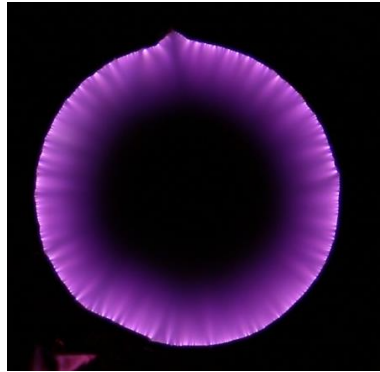


J. Gary Eden and Kazuo Terashima, New plasma sources and regimes, 2017 Plasma Roadmap

Miniaturized ring-type SDBDs

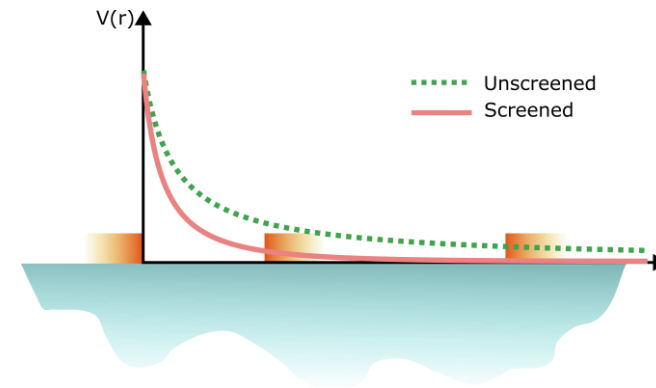


Rodrigues, F., Páscoa, J., pages 1–33. 02 2023

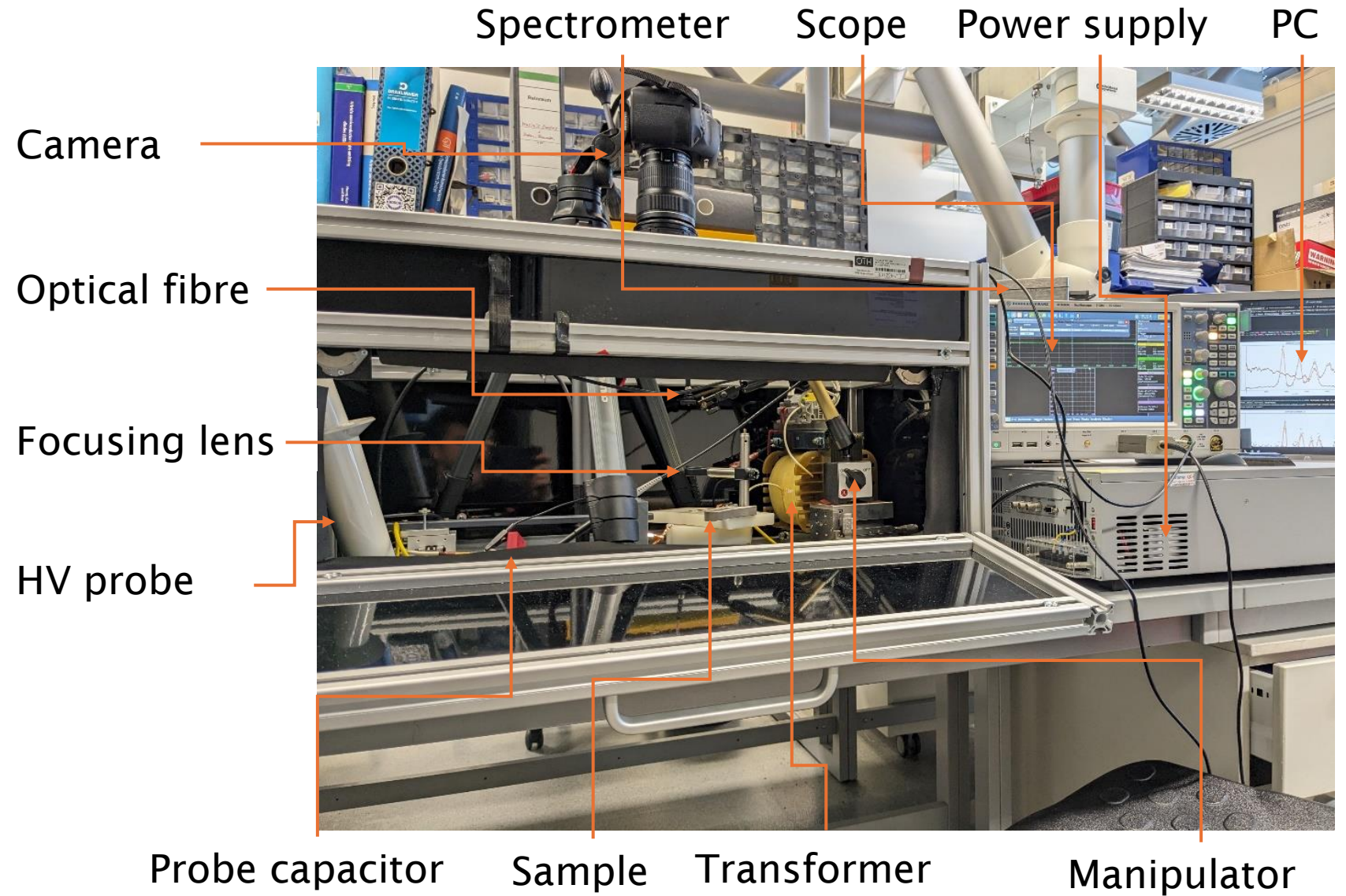
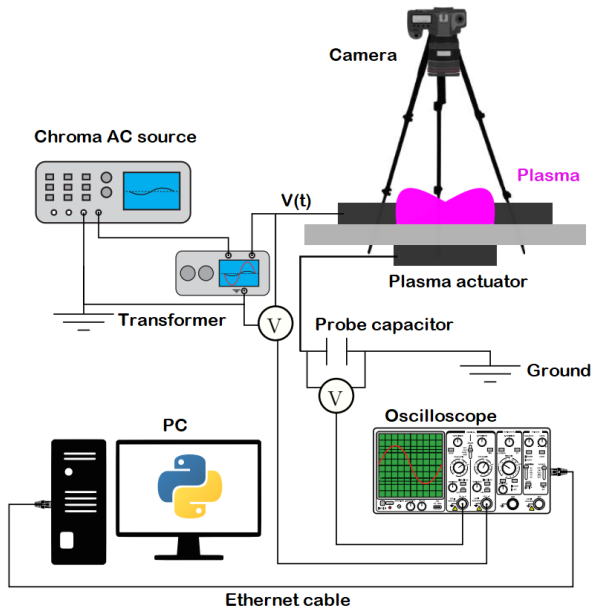


Motivation

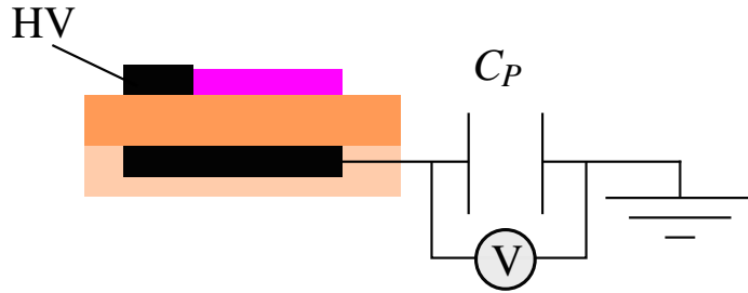
- Induce Perpendicular Ionic Flow
- Eliminate edge effects and fringing fields
- Local effects -> Global w.r.t. dimensions



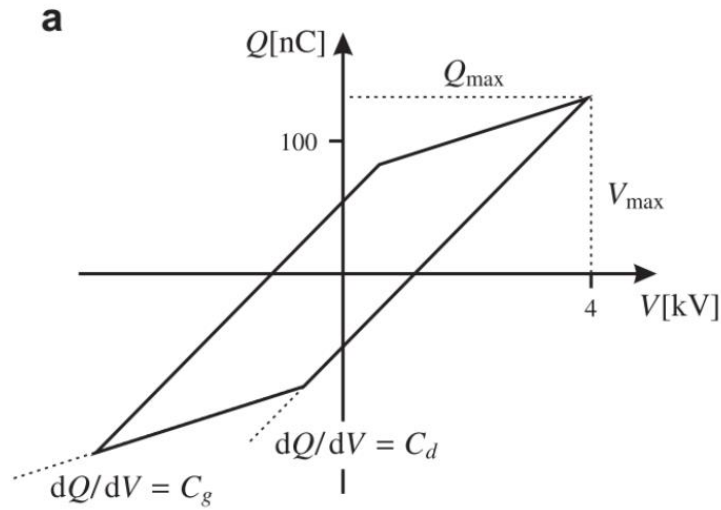
Dielectric material	Dielectric thickness	Electrode material	Electrode thickness	Diameters
Zirconia	150µm	Titanium	550nm	0.4-2 mm



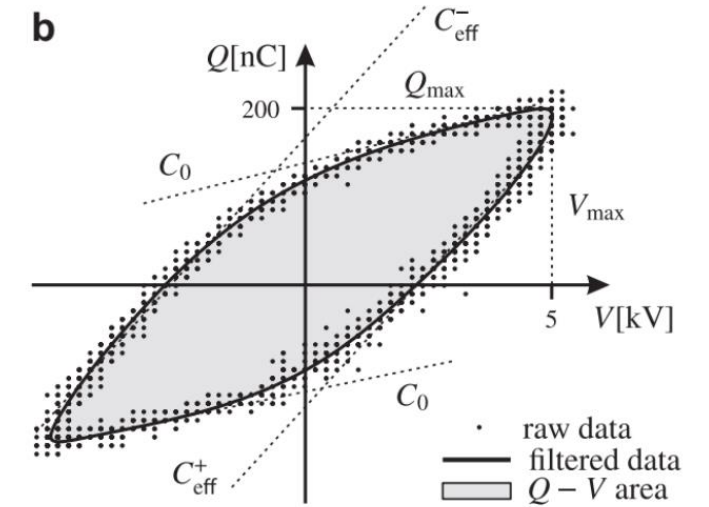
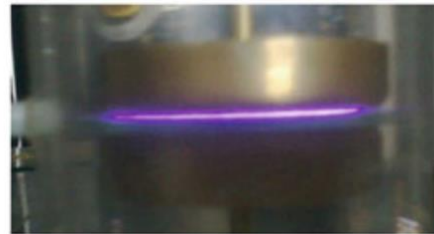
Q-V plots (Lissajous figure)



$$C_{eff.}(t) = \frac{\epsilon_r \epsilon_0 L \cdot W_{eff.}(t)}{d}$$



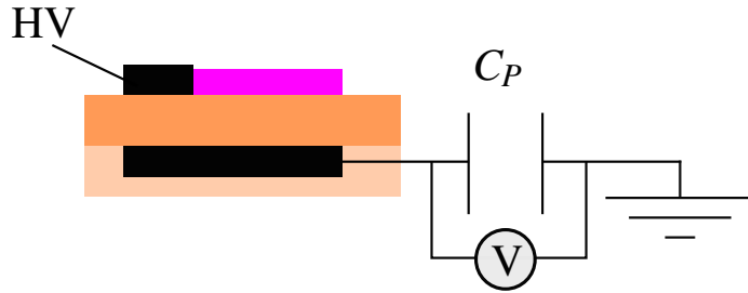
volume discharge (VD);
following Wagner *et al.* [56]



surface discharge (SD);
extracted from Möller [35]



Q-V plots (Lissajous figure)

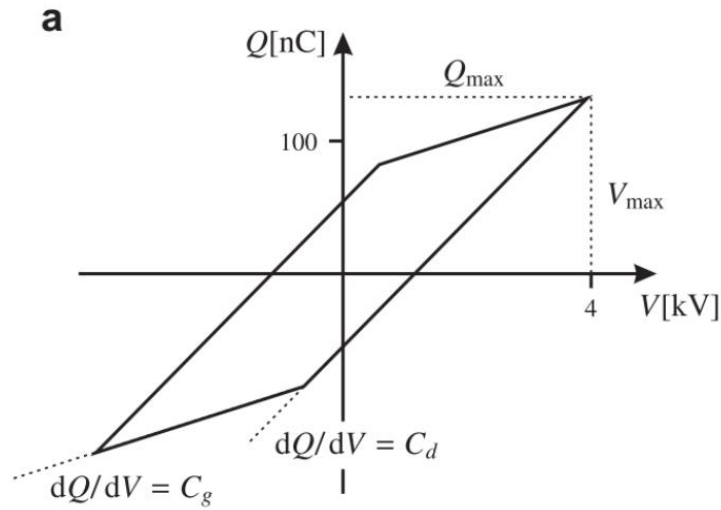


$$P(t) = V(t) \cdot i(t)$$

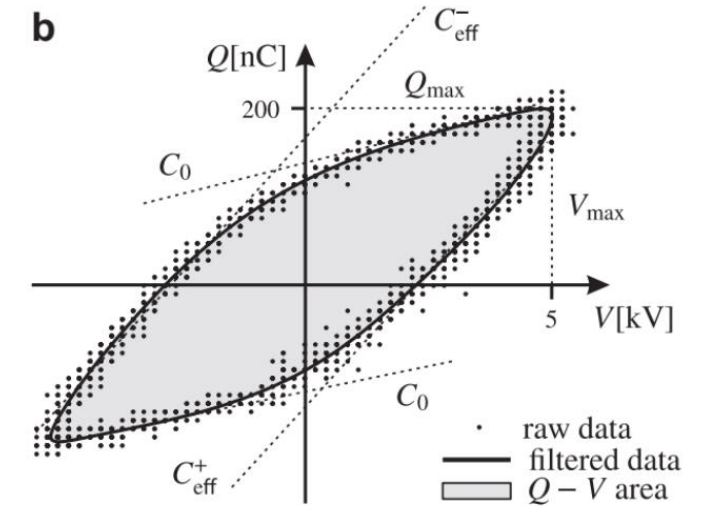
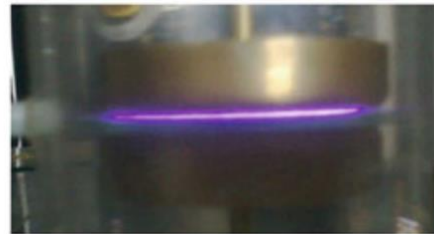
$$= V(t) \cdot$$

$$C_p \frac{dV_p(t)}{dt} = \frac{1}{T} \oint V(t) \cdot C_p \frac{dV_p(t)}{dt} dt$$

$$= \frac{1}{T} \oint V(t) dQ(t)$$



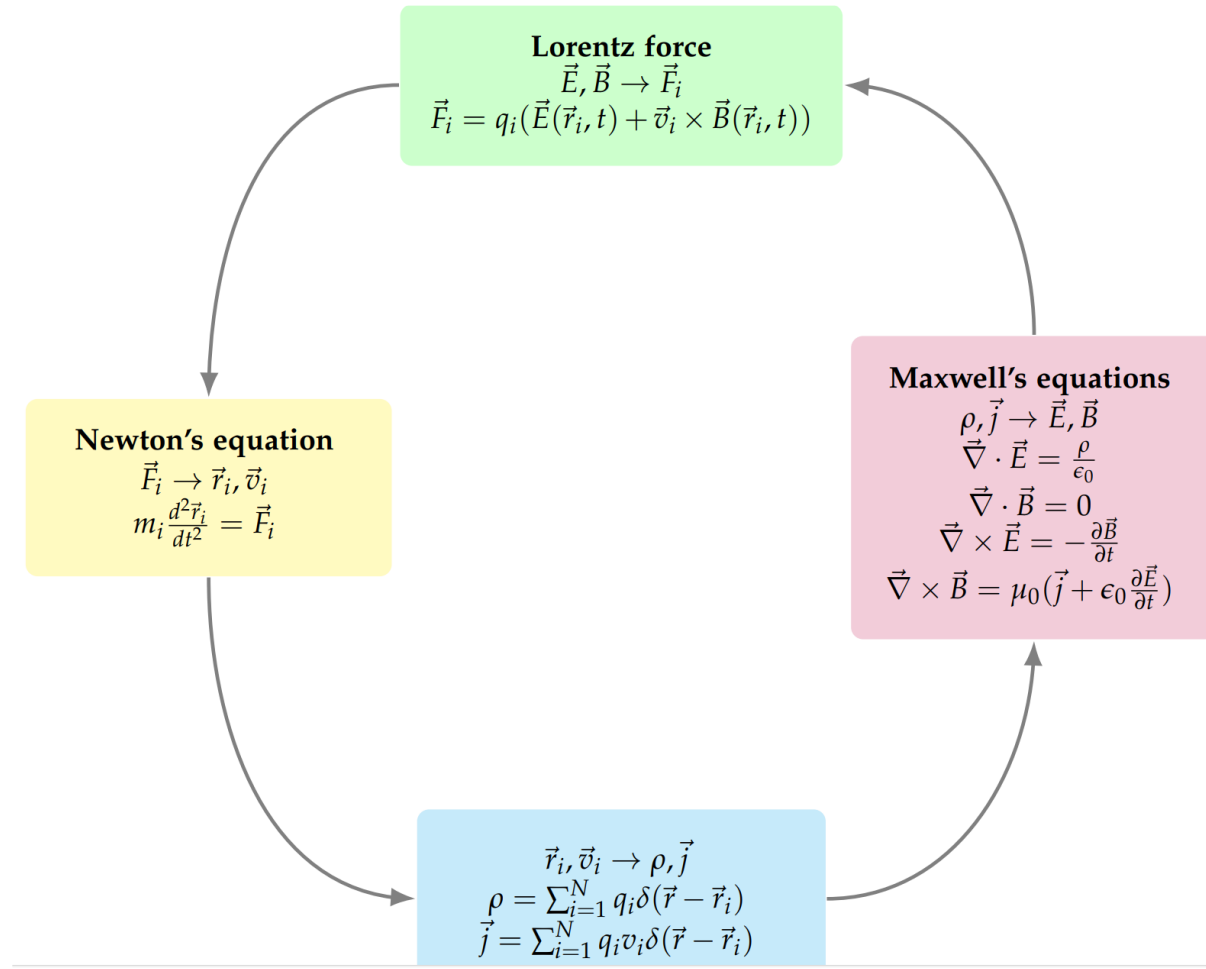
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Self-consistent description of a plasma



Fluid drift-diffusion approach

Rate of electron creation and annihilation

Electron density

Neutral atom density

Energy density

Energy source term

Energy loss/gain

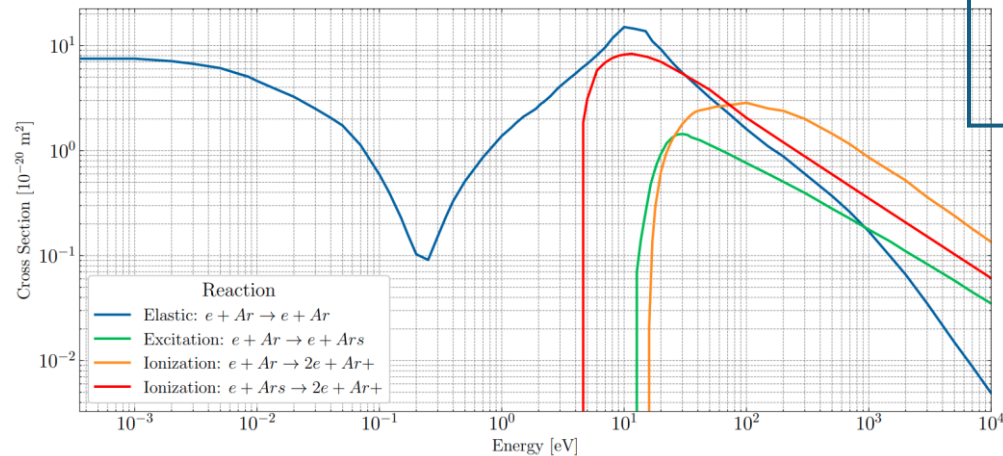
$$R_e = \frac{\partial n_e}{\partial t} + \vec{\nabla} \cdot \vec{\Gamma}_e = \sum_{j=1}^M x_j k_j N_n n_e$$

Molar fractions

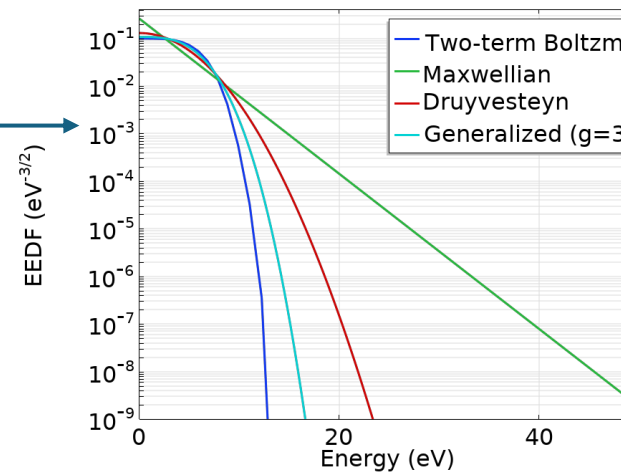
$$S_\epsilon = \frac{\partial n_\epsilon}{\partial t} + \vec{\nabla} \cdot \vec{\Gamma}_\epsilon = \sum_{j=1}^P x_j k_j N_n n_e \Delta$$

Rate constant

$$k_j = \sqrt{\frac{2e}{m_e}} \int_0^\infty \epsilon \sigma_j(\epsilon) f(\epsilon) d\epsilon$$



$$-\nabla^2 V = \frac{\rho_c}{\epsilon_r \epsilon_0} \quad \rho_c = e \left(\sum_{k=1}^N Z_k n_k - n_e \right)$$

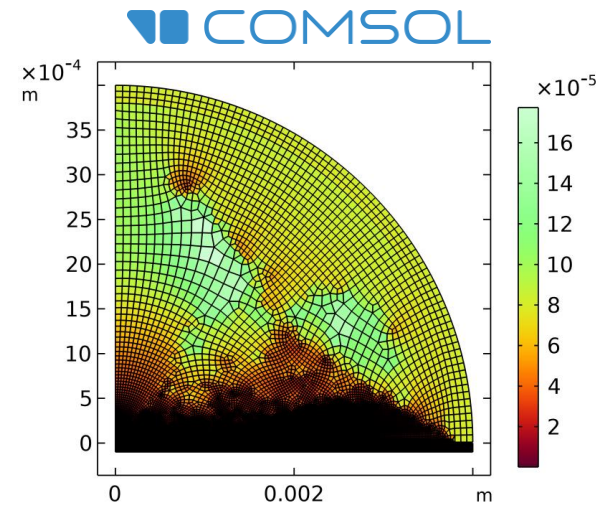


Model

Parameters

- Argon environment
- $V_0 = 500\text{ V}$
- $f_0 = 1\text{ kHz}$
- $\epsilon_r = 5$
- $t = 100\text{ }\mu\text{m}$
- $T_g = 400\text{ K}$
- $p_0 = 1\text{ atm}$
- $\mu_e N_n = 4 \cdot 10^{24} \frac{1}{\text{V} \cdot \text{m} \cdot \text{s}}$
- Maxwellian

Geometry



Chemistry set

Reaction	Formula	Type	$\Delta\epsilon$ (eV)	Forward rate constant ($\text{m}^3/\text{s} \cdot \text{mol}$)
1	$e + \text{Ar} \rightarrow e + \text{Ar}$	Elastic	0	Cross-section
2	$e + \text{Ar} \rightarrow e + \text{Ars}$	Excitation	11.5	Cross-section
3	$e + \text{Ars} \rightarrow e + \text{Ar}$	Superelastic	-11.5	Cross-section
4	$e + \text{Ar} \rightarrow 2e + \text{Ar}^+$	Direct ionization	15.8	Cross-section
5	$e + \text{Ars} \rightarrow 2e + \text{Ar}^+$	Stepwise ionization	4.427	Cross-section
6	$\text{Ars} + \text{Ars} \rightarrow e + \text{Ar} + \text{Ar}^+$	Penning ionization	-	3.734×10^8
7	$\text{Ars} + \text{Ar} \rightarrow \text{Ar} + \text{Ar}$	Metastable quenching	-	1807

Reaction	Formula	Sticking coefficient	Secondary emission coefficient	Mean energy of secondary electron (eV)
1	$\text{Ar}^+ \rightarrow \text{Ar}$	1	0.01	2.5
2	$\text{Ars} \rightarrow \text{Ar}$	1	0	0

Initial and boundary conditions

- Surface charge accumulation along dielectric surface
- Zero charge along outer boundary
- Wall condition along surface

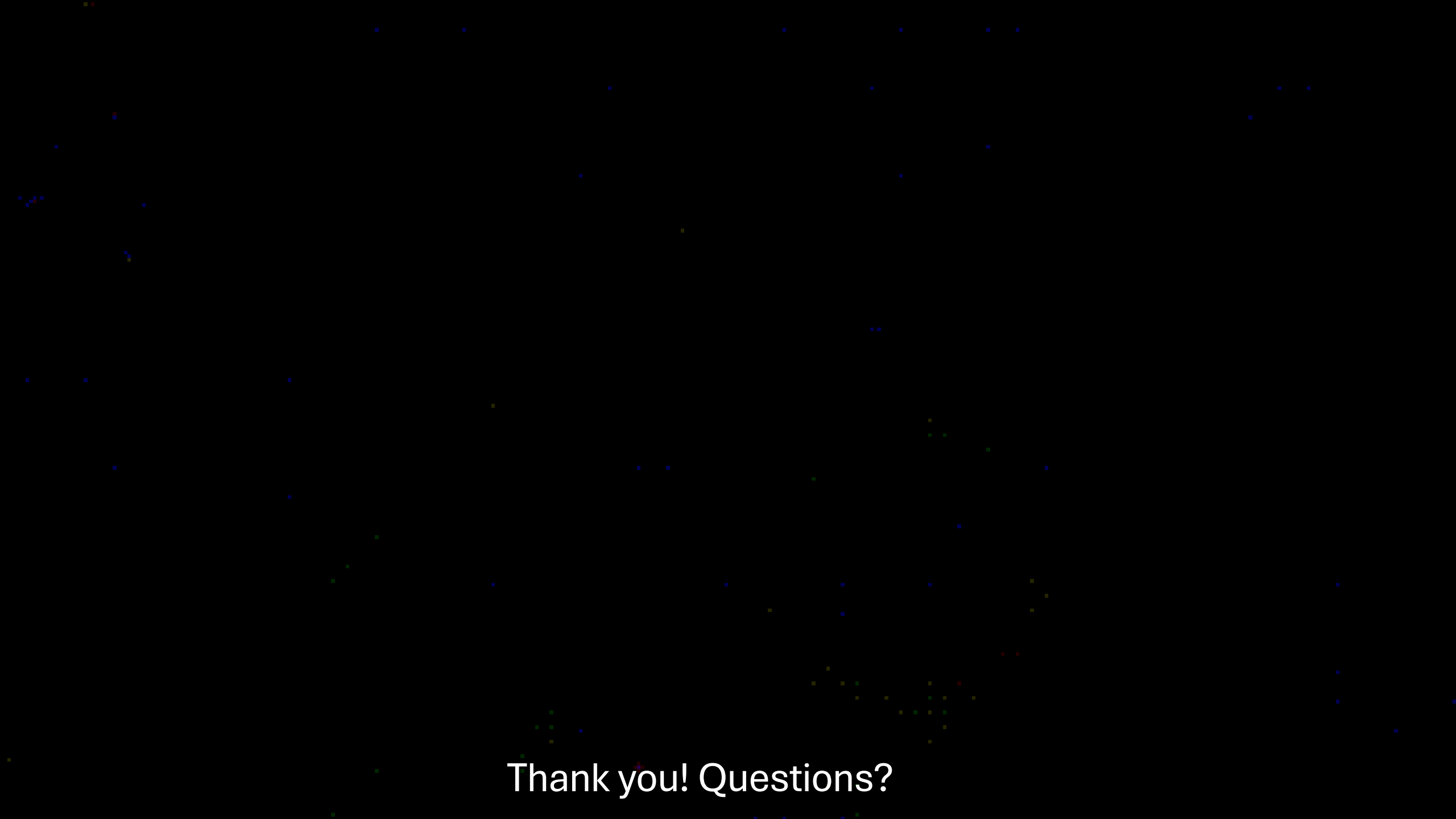
$$-\vec{n} \cdot (\vec{D}_g - \vec{D}_d) = \rho_s$$

$$\frac{d\rho_s}{dt} = \vec{n} \cdot \vec{j}_i + \vec{n} \cdot \vec{j}_e$$

$$-\vec{n} \cdot \vec{D} = 0$$

Conclusion

- Rich Information in Electrical Signals
- Innovative Applications and Technologies
 - Advanced Plasma Diagnostics
 - Miniaturized ion sources
 - Vertical scaling and heterogeneous integration at the chip-level
- Future work:
 - Perform simulations in air
 - Pressure and gas dependent experiments
 - Different dielectric materials with modified surface properties
 - Correlate with other measurement techniques



Thank you! Questions?